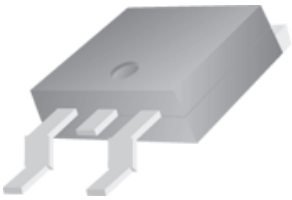
N-Channel 150-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
150	200 @ V_{GS} = 10V	21
	225 @ V_{GS} = 5.5V	20

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology

Pb-free
RoHS COMPLIANT
HALOGEN FREE



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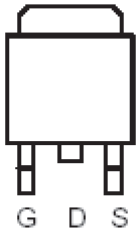

Top View

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[a]	T_C=25°C	I_D	21	A
Pulsed Drain Current[b]		I_{DM}	72	
Continuous Source Current (Diode Conduction)[a]		I_S	20	A
Power Dissipation[a]	T_C=25°C	P_D	125	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient[a]	$R_{\theta JA}$	62.5	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	1	°C/W

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min	**Typ**	**Max**	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA	1.0			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 120 V, V_{GS} = 0 V			1	uA
		V_{DS} = 120 V, V_{GS} = 0 V, T_J = 55°C			25	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = 5.5 V, V_{GS} = 10 V	20			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 2 A			200	mΩ
		V_{GS} = 5.5 V, I_D = 2 A			225	
Forward Tranconductance[A]	g_{fs}	V_{DS} = 40 V, I_D = 2 A		4.4		S
Diode Forward Voltage	V_{SD}	I_S = 2 A, V_{GS} = 0 V		1.1		V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 25 V, V_{GS} = 10 V, I_D = 2 A		16		nC
Gate-Source Charge	Q_{gs}			3		
Gate-Drain Charge	Q_{gd}			9		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 100 V, R_L = 25 Ω , I_D = 9 A, V_{GEN} = 10 V		11		nS
Rise Time	t_r			34		
Turn-Off Delay Time	$t_{d(off)}$			45		
Fall-Time	t_f			77		

Notes

a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.